

MPSW45, MPSW45A

One Watt Darlington Transistors

NPN Silicon

Features

- Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating		Symbol	Value	Unit
Collector - Emitter Voltage	MPSW45 MPSW45A	V_{CES}	40 50	Vdc
Collector - Base Voltage	MPSW45 MPSW45A	V_{CBO}	50 60	Vdc
Emitter - Base Voltage		V_{EBO}	12	Vdc
Collector Current - Continuous		I_C	1.0	Adc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C		P_D	1.0 8.0	W mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C		P_D	2.5 20	W mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range		T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

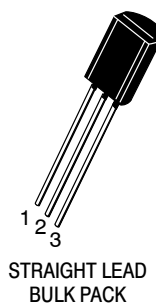
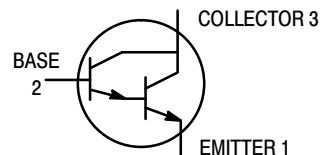
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	125	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	50	$^\circ\text{C/W}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

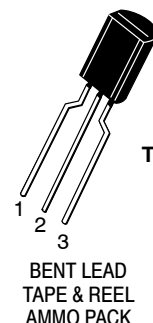


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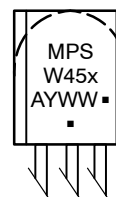


STRAIGHT LEAD
BULK PACK



TO-92 1 WATT
(TO-226)
CASE 29-10
STYLE 1

MARKING DIAGRAM



MPSW45x = Device Code

x = 45A Devices

A = Assembly Location

Y = Year

WW = Work Week

■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MPSW45, MPSW45A

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector – Emitter Breakdown Voltage ($I_C = 100\ \mu\text{Adc}$, $V_{BE} = 0$)	$V_{(BR)CES}$	40 50	– –	Vdc
Collector – Base Breakdown Voltage ($I_C = 100\ \mu\text{Adc}$, $I_E = 0$)	$V_{(BR)CBO}$	50 60	– –	Vdc
Emitter – Base Breakdown Voltage ($I_E = 10\ \mu\text{Adc}$, $I_C = 0$)	$V_{(BR)EBO}$	12	–	Vdc
Collector Cutoff Current ($V_{CB} = 30\ \text{Vdc}$, $I_E = 0$) ($V_{CB} = 40\ \text{Vdc}$, $I_E = 0$)	I_{CBO}	– –	100 100	nAdc
Emitter Cutoff Current ($V_{EB} = 10\ \text{Vdc}$, $I_C = 0$)	I_{EBO}	–	100	nAdc

ON CHARACTERISTICS (Note 1)

DC Current Gain ($I_C = 200\ \text{mAdc}$, $V_{CE} = 5.0\ \text{Vdc}$) ($I_C = 500\ \text{mAdc}$, $V_{CE} = 5.0\ \text{Vdc}$) ($I_C = 1.0\ \text{Adc}$, $V_{CE} = 5.0\ \text{Vdc}$)	h_{FE}	25,000 15,000 4,000	150,000 – –	–
Collector – Emitter Saturation Voltage ($I_C = 1.0\ \text{Adc}$, $I_B = 2.0\ \text{mAdc}$)	$V_{CE(sat)}$	–	1.5	Vdc
Base – Emitter Saturation Voltage ($I_C = 1.0\ \text{Adc}$, $I_B = 2.0\ \text{mAdc}$)	$V_{BE(sat)}$	–	2.0	Vdc
Base – Emitter On Voltage ($I_C = 1.0\ \text{Adc}$, $V_{CE} = 5.0\ \text{Vdc}$)	$V_{BE(on)}$	–	2.0	Vdc

SMALL – SIGNAL CHARACTERISTICS

Current – Gain – Bandwidth Product ($I_C = 200\ \text{mAdc}$, $V_{CE} = 5.0\ \text{Vdc}$, $f = 100\ \text{MHz}$)	f_T	100	–	MHz
Collector – Base Capacitance ($V_{CB} = 10\ \text{Vdc}$, $I_E = 0$, $f = 1.0\ \text{MHz}$)	C_{cb}	–	6.0	pF

1. Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$; Duty Cycle $\leq 2.0\%$.

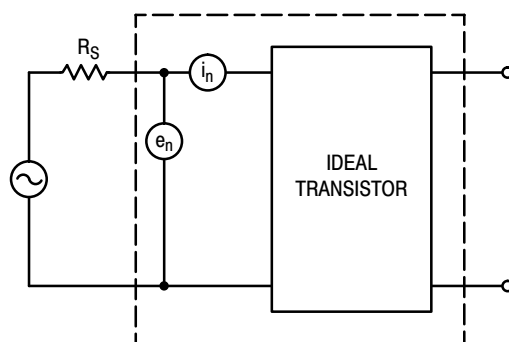


Figure 1. Transistor Noise Model

MPSW45, MPSW45A

NOISE CHARACTERISTICS

($V_{CE} = 5.0 \text{ Vdc}$, $T_A = 25^\circ\text{C}$)

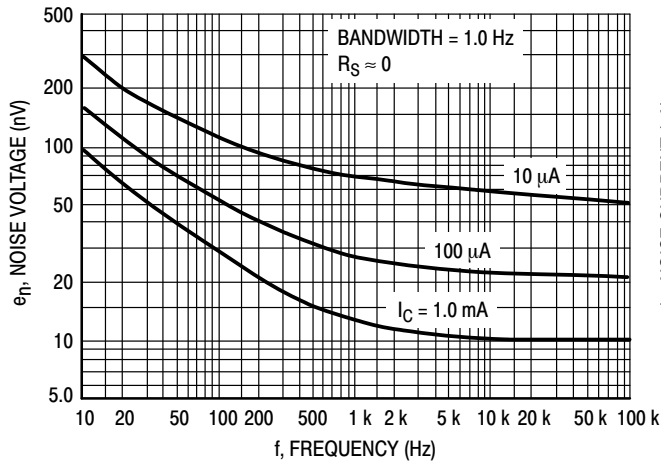


Figure 2. Noise Voltage

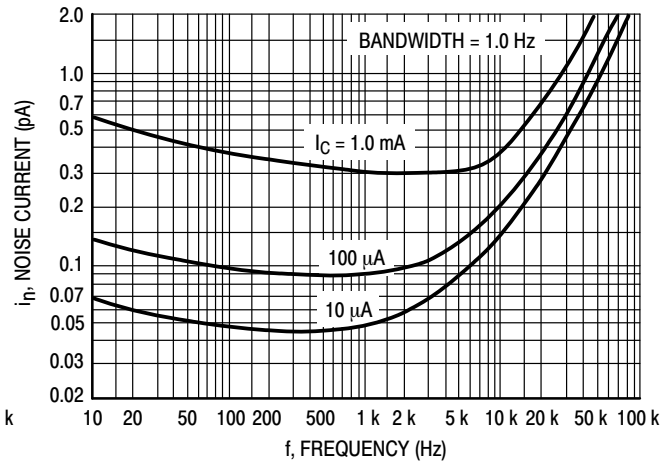


Figure 3. Noise Current

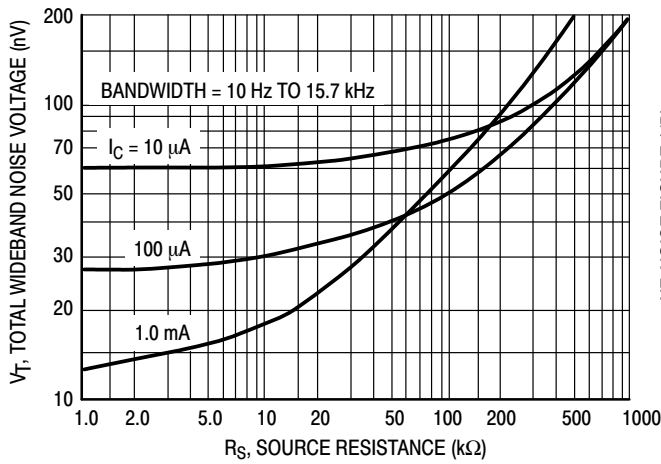


Figure 4. Total Wideband Noise Voltage

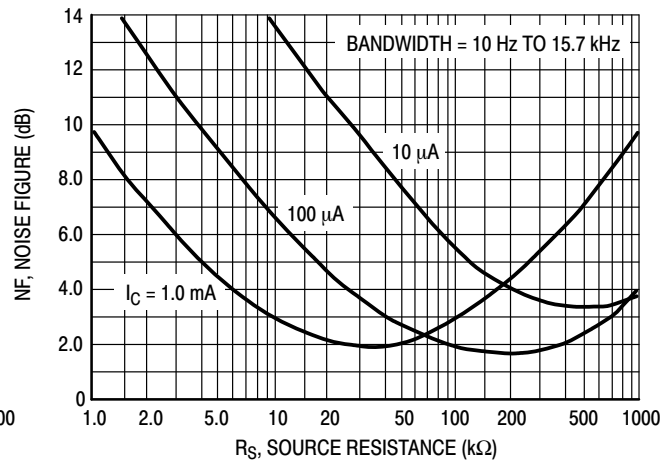


Figure 5. Wideband Noise Figure

MPSW45, MPSW45A

SMALL-SIGNAL CHARACTERISTICS

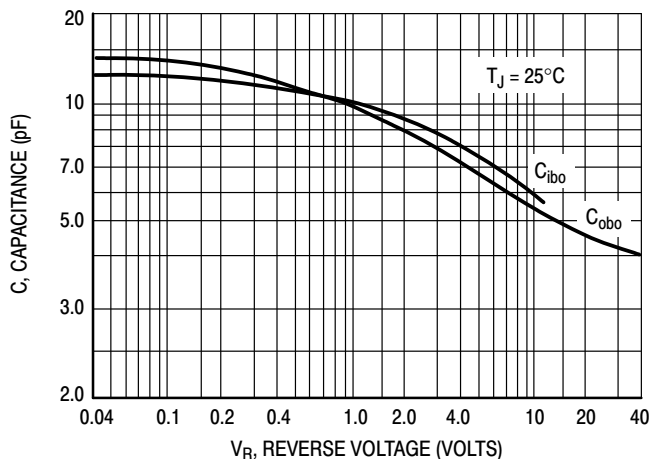


Figure 6. Capacitance

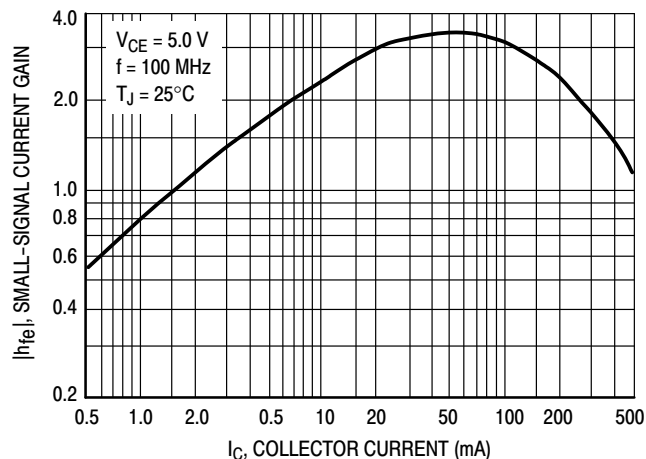


Figure 7. High Frequency Current Gain

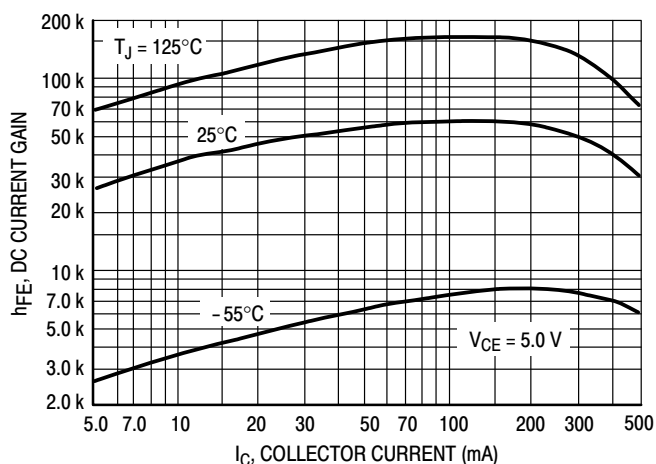


Figure 8. DC Current Gain

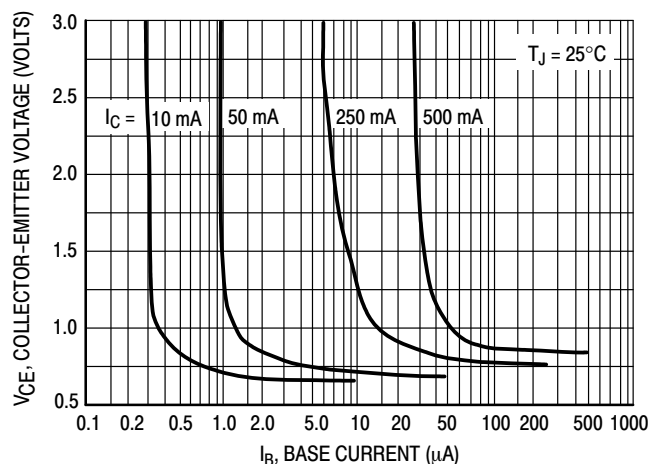


Figure 9. Collector Saturation Region

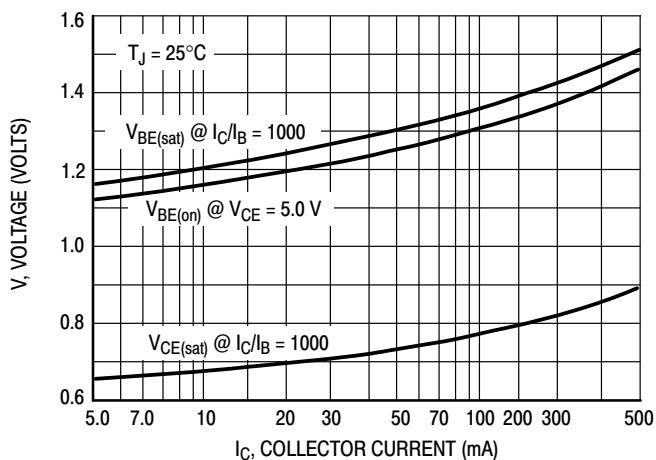


Figure 10. "On" Voltages

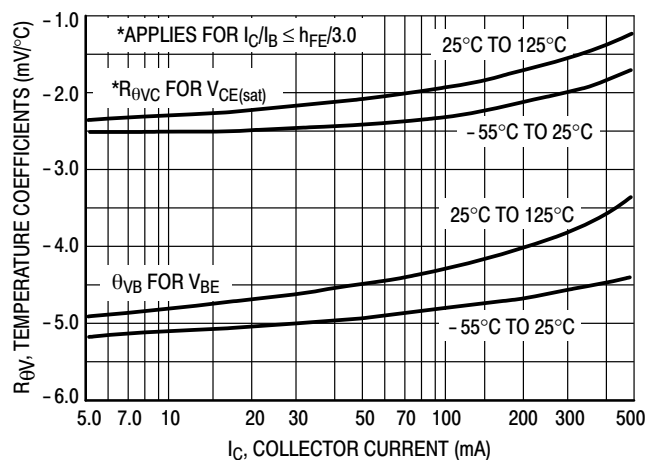


Figure 11. Temperature Coefficients

MPSW45, MPSW45A

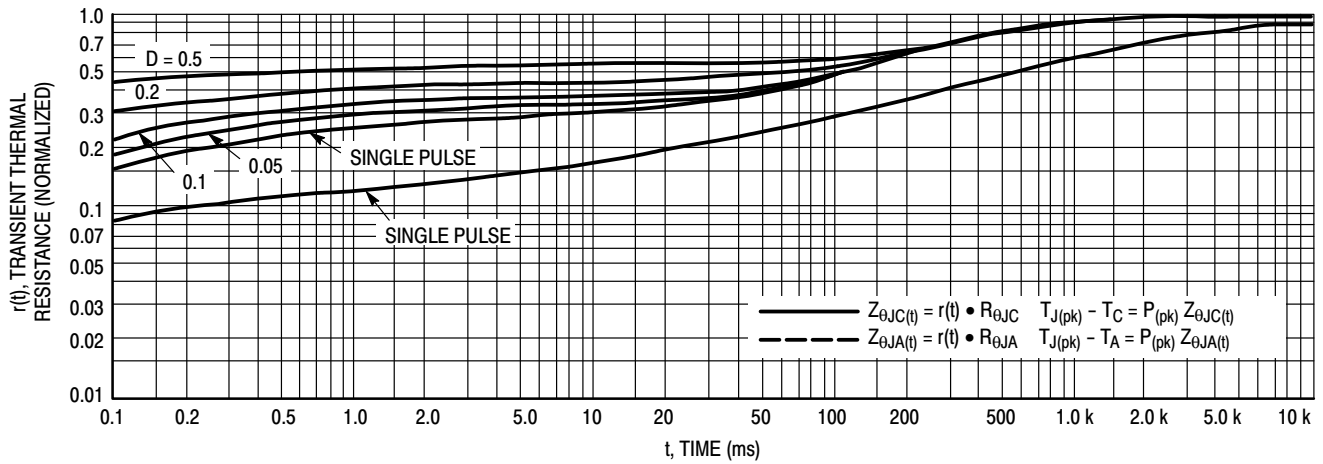


Figure 12. Thermal Response

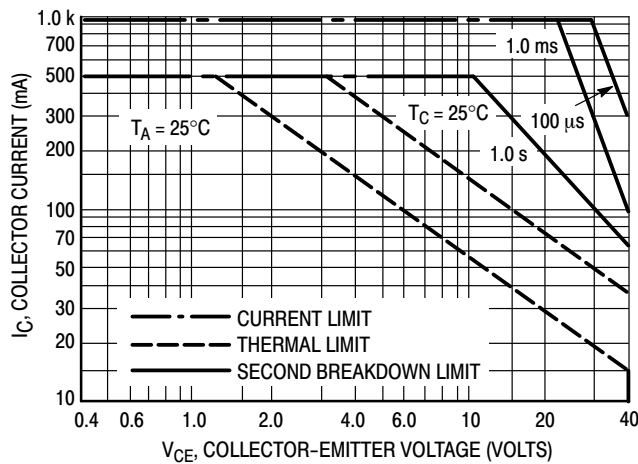
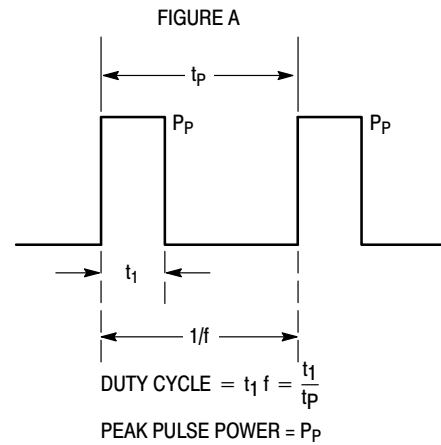


Figure 13. Active Region Safe Operating Area



Design Note: Use of Transient Thermal Resistance Data

ORDERING INFORMATION

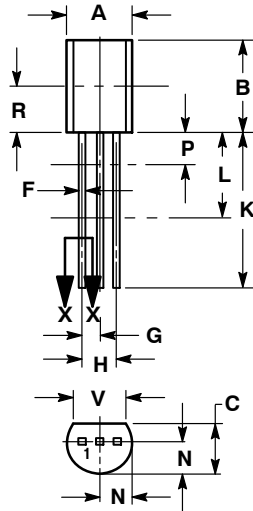
Device	Package	Shipping [†]
MPSW45G	TO-92 (Pb-Free)	5,000 Units / Box
MPSW45RLREG	TO-92 (Pb-Free)	2,000 / Tape & Reel
MPSW45A	TO-92	5,000 Units / Box
MPSW45AG	TO-92 (Pb-Free)	5,000 Units / Box
MPSW45ARLRA	TO-92	2,000 / Tape & Reel
MPSW45ARLRAG	TO-92 (Pb-Free)	2,000 / Tape & Reel
MPSW45AZL1	TO-92	2,000 / Ammo Pack
MPSW45AZL1G	TO-92 (Pb-Free)	2,000 / Ammo Pack

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

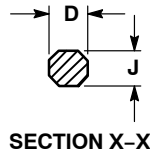
MPSW45, MPSW45A

PACKAGE DIMENSIONS

TO-92 (TO-226) 1 WATT
CASE 29-10
ISSUE O



STRAIGHT LEAD
BULK PACK

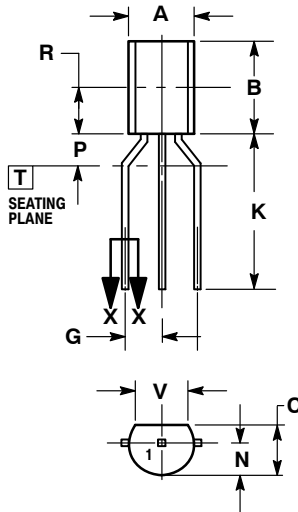


NOTES:

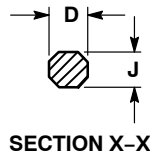
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. DIMENSION F APPLIES BETWEEN DIMENSIONS P AND L. DIMENSIONS D AND J APPLY BETWEEN DIMENSIONS L AND K MINIMUM. THE LEAD DIMENSIONS ARE UNCONTROLLED IN DIMENSION P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.44	5.21
B	0.290	0.310	7.37	7.87
C	0.125	0.165	3.18	4.19
D	0.018	0.021	0.46	0.53
F	0.016	0.019	0.41	0.48
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.018	0.024	0.46	0.61
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.135	---	3.43	---
V	0.135	---	3.43	---

STYLE 1:
PIN 1. EMITTER
2. BASE
3. COLLECTOR



BENT LEAD
TAPE & REEL
AMMO PACK



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. DIMENSION F APPLIES BETWEEN DIMENSIONS P AND L. DIMENSIONS D AND J APPLY BETWEEN DIMENSIONS L AND K MINIMUM. THE LEAD DIMENSIONS ARE UNCONTROLLED IN DIMENSION P AND BEYOND DIMENSION K MINIMUM.

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D	0.018	0.021	0.46	0.53
G	0.094	0.102	2.40	2.80
J	0.018	0.024	0.46	0.61
K	0.500	---	12.70	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.135	---	3.43	---
V	0.135	---	3.43	---

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- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
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- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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